

P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	Package	I _D T _A = +25°C
-50V	8Ω @ V _{GS} = -5V	X1-DFN1006-3	-310A

Description

This new generation MOSFET has been designed to minimize the onstate resistance $(R_{DS(on)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power management functions
- · Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected 1kV
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

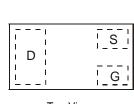
- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight: 0.001 grams (approximate)



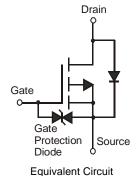




Bottom View



Top View Pin-Out



Ordering Information (Note 4)

Part Number	Case	Packaging		
DMP58D0LFB-7	X1-DFN1006-3	3,000 / Tape & Reel		
DMP58D0LFB-7B	X1-DFN1006-3	10,000 / Tape & Reel		

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information





Top View Dot Denotes Drain Side

DMP58D0LFB-7B



Top View Bar Denotes Gate and Source Side

NZ = Product Type Marking Code



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Character	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	-50	V		
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Drain Current (Note 4) V _{GS} = -5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-180 -150	mA
Continuous Drain Current (Note 5) $V_{GS} = -5V$ Steady $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$			I _D	-310 -250	mA
Pulsed Drain Current (Note 6)	I _{DM}	-500	mA		

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 4)	P _D	0.47	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 4)	$R_{\theta JA}$	258	°C/W
Power Dissipation (Note 5)	P _D	1.22	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	$R_{\theta JA}$	105	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

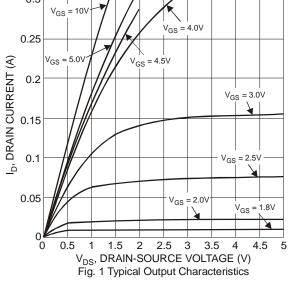
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

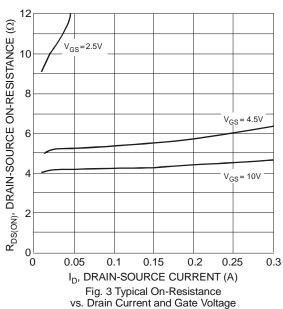
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage		-50			V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current T _J = 25°C			_	-1.0	μA	$V_{DS} = -50V, V_{GS} = 0V$
Gate-Source Leakage				±5	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	-0.8		-2.1	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
Static Drain-Source On-Resistance	Б	_	6	8	Ω	$V_{GS} = -5V, I_{D} = -100mA$
Static Drain-Source On-Resistance	R _{DS (ON)}	_	12	18	Ω	$V_{GS} = -2.5V, I_{D} = -10mA$
Forward Transfer Admittance	Y _{fs}	0.05	_	_	S	$V_{DS} = -25V, I_{D} = -100mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	_	27	_		
Output Capacitance	Coss	_	4.0	_	pF	$V_{DS} = -25V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	C_{rss}	_	1.4	_		1 = 1.000112
Turn-On Delay Time	t _{D(on)}	_	30.7	_		
Turn-On Rise Time	t _r	_	84.1	_		$V_{GS} = -4.5V, V_{DS} = -30V,$
Turn-Off Delay Time	t _{D(off)}	_	201.8	_	ns	$R_G = 50\Omega$, $I_D = -10$ mA
Turn-Off Fall Time	t _f	_	32.2	_		

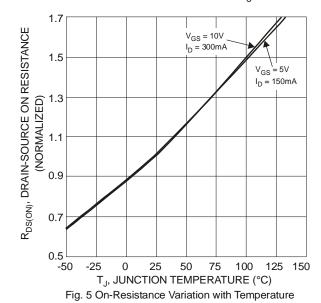
Notes:

- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate
 Repetitive rating, pulse width limited by junction temperature.
- 7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to production testing.

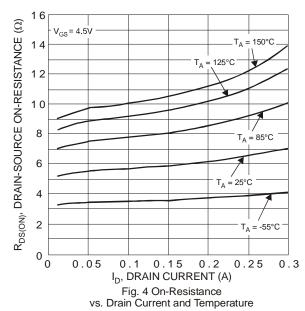


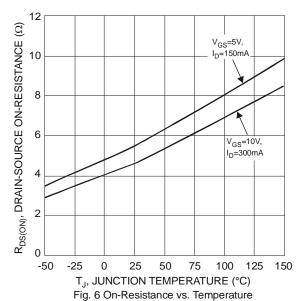






0.3 $V_{GS} = 5V$ 0.25 = 25°C ID, DRAIN CURRENT (A) 125°C 0.2 0.15 0.1 0.05 0 0.5 1.5 2 2.5 3 3.5 0 V_{GS}, GATE SOURCE VOLTAGE (V) Fig. 2 Typical Transfer Characteristics







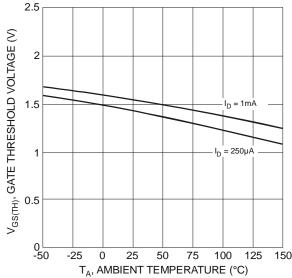


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

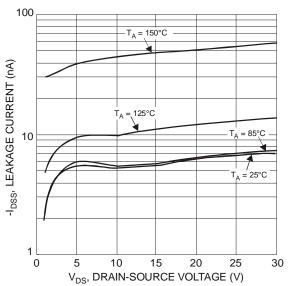
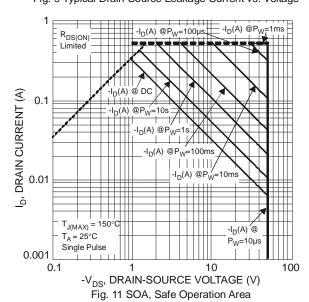
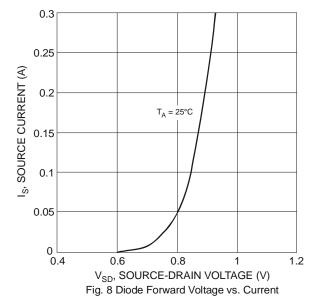
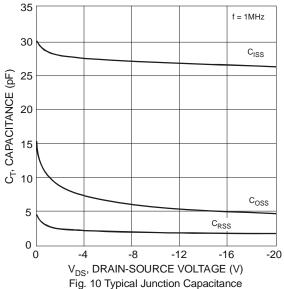


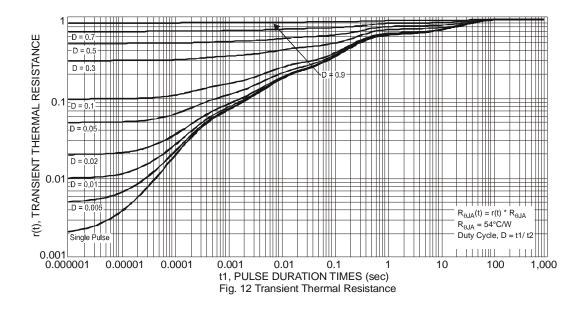
Fig. 9 Typical Drain-Source Leakage Current vs. Voltage





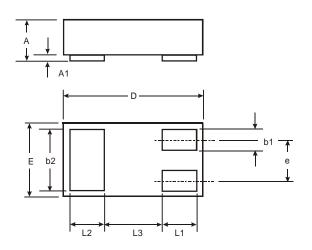






Package Outline Dimensions

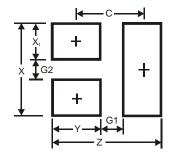
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



X1-DFN1006-3					
Dim	Min	Max	Тур		
Α	0.47	0.53	0.50		
A1	0	0.05	0.03		
b1	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.075	1.00		
Е	0.55	0.675	0.60		
e			0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3			0.40		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
Z	1.1		
G1	0.3		
G2	0.2		
Х	0.7		
X1	0.25		
Υ	0.4		
С	0.7		



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2012, Diodes Incorporated

www.diodes.com